## 2N6338，2N6341

## High－Power NPN Silicon <br> Transistors

．．．designed for use in industrial－military power amplifier and switching circuit applications．
－High Collector－Emitter Sustaining Voltage－

$$
\begin{aligned}
& \mathrm{V}_{\mathrm{CEO}(\mathrm{sus})}=100 \mathrm{Vdc}(\mathrm{Min})-2 \mathrm{~N} 6338 \\
& =150 \mathrm{Vdc}(\mathrm{Min})-2 \mathrm{~N} 6341
\end{aligned}
$$

－High DC Current Gain－

$$
\begin{aligned}
\mathrm{h}_{\mathrm{FE}}=30 & -120 @ \mathrm{I}_{\mathrm{C}}=10 \text { Adc } \\
& =12(\mathrm{Min}) @ \mathrm{I}_{\mathrm{C}}=25 \text { Adc }
\end{aligned}
$$

－Low Collector－Emitter Saturation Voltage－

$$
\mathrm{V}_{\mathrm{CE}(\mathrm{sat})}=1.0 \mathrm{Vdc}(\mathrm{Max}) @ \mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}
$$

－Fast Switching Times＠ $\mathrm{I}_{\mathrm{C}}=10$ Adc

$$
\begin{aligned}
& \mathrm{t}_{\mathrm{r}}=0.3 \mathrm{~ms}(\mathrm{Max}) \\
& \mathrm{t}_{\mathrm{s}}=1.0 \mathrm{~ms}(\mathrm{Max}) \\
& \mathrm{t}_{\mathrm{f}}=0.25 \mathrm{~ms}(\mathrm{Max})
\end{aligned}
$$

－ Pb －Free Packages are Available
＊MAXIMUM RATINGS

| Rating | Symbol | 2N6338 | 2N6341 | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Collector－Base Voltage | $\mathrm{V}_{\mathrm{CB}}$ | 120 | 180 | Vdc |
| Collector－Emitter Voltage | $\mathrm{V}_{\mathrm{CEO}}$ | 100 | 150 | Vdc |
| Emitter－Base Voltage | $\mathrm{V}_{\mathrm{EB}}$ | 6.0 | Vdc |  |
| Collector Current <br> Continuous <br> Peak | $\mathrm{I}_{\mathrm{C}}$ | 25 |  | Adc |
| Base Current |  | 50 |  |  |
| Total Device Dissipation <br> ＠ <br> Derate above $25^{\circ}{ }^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 200 | W |  |
| Operating and Storage <br> Junction <br> Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to＋200 | ${ }^{\circ} \mathrm{C}$ |  |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: |
| Thermal Resistance，Junction to Case | $\theta_{\text {JC }}$ | 0.875 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding Maximum Ratings may damage the device．Maximum Ratings are stress ratings only．Functional operation above the Recommended Operating Conditions is not implied．Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability．
＊Indicates JEDEC Registered Data．

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## 25 AMPERE POWER TRANSISTORS NPN SILICON



TO－204AA CASE 1－07

ORDERING INFORMATION

| Device | Package | Shipping |
| :--- | :---: | :---: |
| 2N6338 | TO－204AA | 100 Units／Tray |
| 2N6338G | TO－204AA <br> （Pb－Free） | 100 Units／Tray |
| 2N6341 | TO－204AA | 100 Units／Tray |
| 2N6341G | TO－204AA <br> （Pb－Free） | 100 Units／Tray |

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胜特力 电子（上海）86－21－34970699胜特力 电子（深圳）86－755－83298787

Http：／／www． $100 y$ ．com．tw


Figure 1. Power Derating
*ELECTRICAL CHARACTERISTICS $\left(T_{C}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Sustaining Voltage (1) $\left(\mathrm{I}_{\mathrm{C}}=50 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\begin{aligned} & \hline \text { 2N6338 } \\ & \text { 2N6341 } \end{aligned}$ | $\mathrm{V}_{\text {CEO(sus) }}$ | $\begin{aligned} & 100 \\ & 150 \end{aligned}$ |  | Vdc |
| Collector Cutoff Current $\left(\mathrm{V}_{\mathrm{CE}}=50 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ $\left(\mathrm{V}_{\mathrm{CE}}=75 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\begin{aligned} & \text { 2N6338 } \\ & \text { 2N6341 } \end{aligned}$ | ICEO | - | $\begin{aligned} & 50 \\ & 50 \end{aligned}$ | $\mu \mathrm{Adc}$ |
| Collector Cutoff Current $\begin{aligned} & \left(\mathrm{V}_{\mathrm{CE}}=\text { Rated } \mathrm{V}_{\mathrm{CEO}}, \mathrm{~V}_{\mathrm{EB}(\text { off })}=1.5 \mathrm{Vdc}\right) \\ & \left(\mathrm{V}_{\mathrm{CE}}=\text { Rated } \mathrm{V}_{\mathrm{CEO}}, \mathrm{~V}_{\mathrm{EB}(\text { off })}=1.5 \mathrm{Vdc}, \mathrm{~T}_{\mathrm{C}}=150^{\circ} \mathrm{C}\right) \end{aligned}$ |  | $I_{\text {CEX }}$ | - | $\begin{aligned} & 10 \\ & 1.0 \end{aligned}$ | $\mu$ Adc <br> mAdc |
| Collector Cutoff Current ( $\mathrm{V}_{\mathrm{CB}}=$ Rated $\left.\mathrm{V}_{\mathrm{CB}}, \mathrm{I}_{\mathrm{E}}=0\right)$ |  | ICBO | - | 10 | $\mu \mathrm{Adc}$ |
| Emitter Cutoff Current ( $\mathrm{V}_{\mathrm{BE}}=6.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0$ ) |  | $\mathrm{I}_{\text {ebo }}$ | - | 100 | $\mu \mathrm{Adc}$ |

ON CHARACTERISTICS (1)

| DC Current Gain) $\begin{aligned} & \left(I_{\mathrm{C}}=0.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{Vdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{Vdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=25 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{Vdc}\right) \end{aligned}$ | $\mathrm{h}_{\text {FE }}$ | $\begin{aligned} & 50 \\ & 30 \\ & 12 \end{aligned}$ | $\begin{gathered} - \\ 120 \end{gathered}$ | - |
| :---: | :---: | :---: | :---: | :---: |
| Collector Emitter Saturation Voltage $\begin{aligned} & \left(I_{C}=10 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{Adc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=25 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=2.5 \mathrm{Adc}\right) \end{aligned}$ | $\mathrm{V}_{\text {CE(sat) }}$ | - | $\begin{aligned} & 1.0 \\ & 1.8 \end{aligned}$ | Vdc |
| Base-Emitter Saturation Voltage $\begin{aligned} & \left(I_{C}=10 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{Adc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=25 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=2.5 \mathrm{Adc}\right) \end{aligned}$ | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ | - | $\begin{aligned} & 1.8 \\ & 2.5 \end{aligned}$ | Vdc |
| Base-Emitter On Voltage ( $\mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=2.0 \mathrm{Vdc}$ ) | $\mathrm{V}_{\mathrm{BE} \text { (on) }}$ | - | 1.8 | Vdc |

DYNAMIC CHARACTERISTICS

| Current-Gain - Bandwidth Product (2) $\quad\left(\mathrm{I}_{\mathrm{C}}=1.0 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=10 \mathrm{Vdc}, \mathrm{f}_{\text {test }}=10 \mathrm{MHz}\right)$ | $\mathrm{f}_{\mathrm{T}}$ | 40 | - | MHz |
| :--- | :--- | :---: | :---: | :---: | :---: |
| Output Capacitance $\left(\mathrm{V}_{\mathrm{CB}}=10 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=0.1 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{ob}}$ | - | 300 | pF |

## SWITCHING CHARACTERISTICS

| Rise Time $\left(\mathrm{V}_{\mathrm{CC}} \approx 80 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}, \mathrm{I}_{\mathrm{B} 1}=1.0 \mathrm{Adc}, \mathrm{V}_{\mathrm{BE}(\mathrm{off})}=6.0 \mathrm{Vdc}\right)$ | $\mathrm{t}_{\mathrm{r}}$ | - | 0.3 | $\mu \mathrm{~s}$ |
| :--- | :---: | :---: | :---: | :---: |
| Storage Time $\left(\mathrm{V}_{\mathrm{Cc}} \approx 80 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}, \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=1.0 \mathrm{Adc}\right)$ | $\mathrm{t}_{\mathrm{s}}$ | - | 1.0 | $\mu \mathrm{~s}$ |
| Fall Time $\left(\mathrm{V}_{\mathrm{CC}} \approx 80 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=10 \mathrm{Adc}, \mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=1.0 \mathrm{Adc}\right)$ | $\mathrm{t}_{\mathrm{f}}$ | - | 0.25 | $\mu \mathrm{~s}$ |

*Indicates JEDEC Registered Data.
(1) Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2.0 \%$.
(2) $\mathrm{f}_{\mathrm{T}}=\left|\mathrm{h}_{\mathrm{f}}\right| \bullet \mathrm{f}_{\text {test }}$.


Figure 2. Switching Time Test Circuit


Figure 4. Thermal Response


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $\mathrm{I}_{\mathrm{C}}-\mathrm{V}_{\mathrm{CE}}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}=200^{\circ} \mathrm{C}$; $\mathrm{T}_{\mathrm{C}}$ is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to $10 \%$ provided $\mathrm{T}_{\mathrm{J}(\mathrm{pk})}$ $\leq 200^{\circ} \mathrm{C} . \mathrm{T}_{\mathrm{J}(\mathrm{pk})}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.


Figure 6. Turn-Off Time


Figure 7. Capacitance

## 2N6338, 2N6341

## PACKAGE DIMENSIONS

## TO-204AA (TO-3

CASE 1-07
ISSUE Z


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY

| DIM | INCHES |  | MILLIMETERS |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN |  | MAX | MIN |  |
| A | 1.550 REF |  | 39.37 REF |  |  |
| B | --- | 1.050 | --- | 26.67 |  |
| C | 0.250 | 0.335 | 6.35 | 8.51 |  |
| D | 0.038 | 0.043 | 0.97 | 1.09 |  |
| E | 0.055 | 0.070 | 1.40 |  | 1.77 |
| G | 0.430 BSC |  | 10.92 BSC |  |  |
| H | 0.215 BSC |  | 5.46 |  | BSC |
| K | 0.440 |  | 0.480 | 11.18 |  |
| L | 0.665 |  | BSC | 16.89 |  |

STYLE 1:
PIN 1. BASE
2. EMITTER

CASE: COLLECTOR


#### Abstract

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